

## N-Channel 20-V (D-S) MOSFET

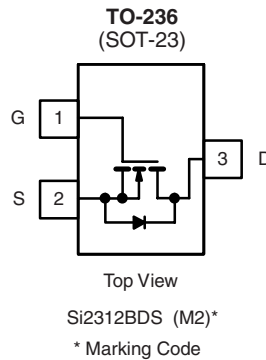
PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)	$Q_g$ (Typ.)
20	0.031 at $V_{GS} = 4.5$ V	5.0	7.5
	0.037 at $V_{GS} = 2.5$ V	4.6	
	0.047 at $V_{GS} = 1.8$ V	4.1	

### FEATURES

- Halogen-free Option Available
- TrenchFET<sup>®</sup> Power MOSFET
- 100 %  $R_g$  Tested



**RoHS**  
COMPLIANT



Ordering Information: Si2312BDS-T1-E3 (Lead (Pb)-free)  
Si2312BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	20		V	
Gate-Source Voltage	$V_{GS}$	$\pm 8$			
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	5.0	3.9	A
		$T_A = 70$ °C	4.0	3.1	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	15			
Avalanche Current <sup>b</sup>	$I_{AS}$	13			
Single Avalanche Energy	$E_{AS}$	8.45		mJ	
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	1.0	0.63	A	
Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	1.25	0.75	W
		$T_A = 70$ °C	0.80	0.48	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 5$ s	80	100	°C/W
		Steady State	120	166	
Maximum Junction-to-Foot	$R_{thJF}$	50	60		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.  
b. Pulse width limited by maximum junction temperature.



SPECIFICATIONS $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	20			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.45		0.85	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			75	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 4.5\text{ V}$	15			A
Drain-Source On-Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 5.0\text{ A}$		0.025	0.031	$\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 4.6\text{ A}$		0.030	0.037	
		$V_{GS} = 1.8\text{ V}, I_D = 4.1\text{ A}$		0.036	0.047	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 5.0\text{ A}$		30		S
Diode Forward Voltage	$V_{SD}$	$I_S = 1.0\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5.0\text{ A}$		7.5	12	nC
Gate-Source Charge	$Q_{gs}$			1.4		
Gate-Drain Charge	$Q_{gd}$			1.2		
Gate Resistance	$R_g$	$f = 1.0\text{ MHz}$	1.1	2.2	3.3	$\Omega$
<b>Switching</b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1.0\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 6\text{ }\Omega$		9	15	ns
Rise Time	$t_r$			30	45	
Turn-Off Delay Time	$t_{d(off)}$			35	55	
Fall Time	$t_f$			10	15	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 1.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		13	25	nC
Body Diode Reverse Recovery Charge	$Q_{rr}$			4.5	7	

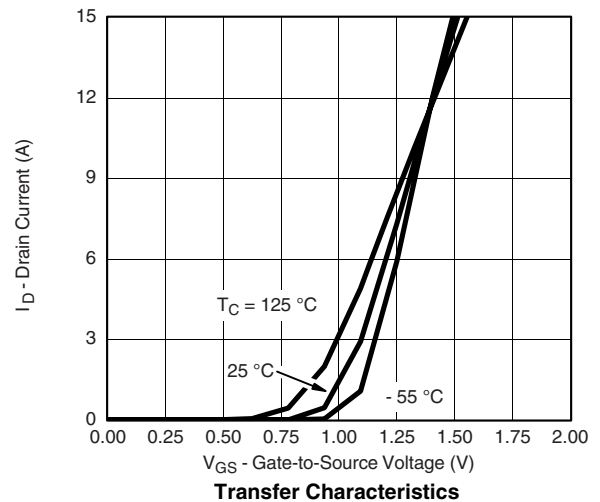
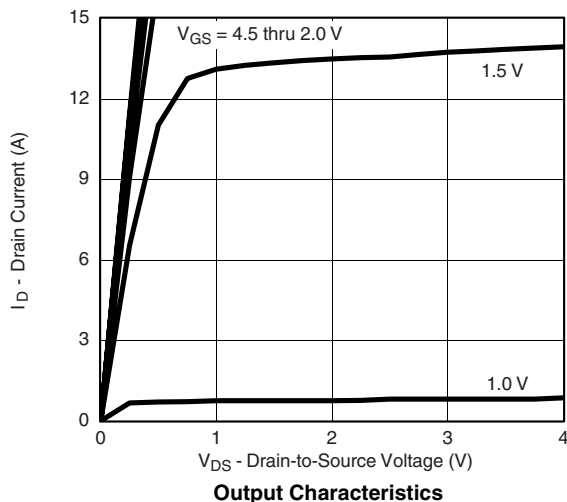
Notes:

a. Pulse test: Pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

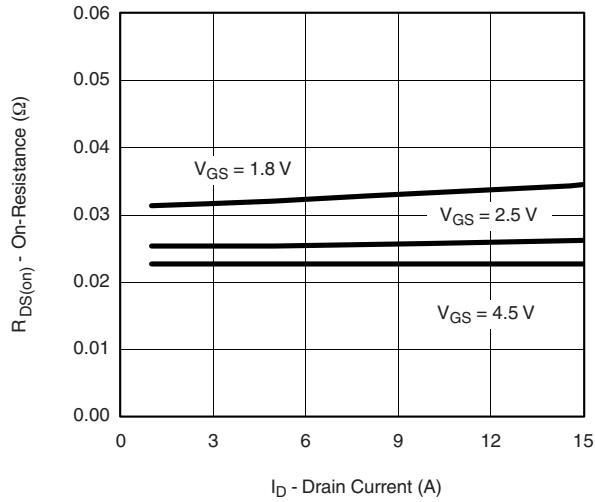
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

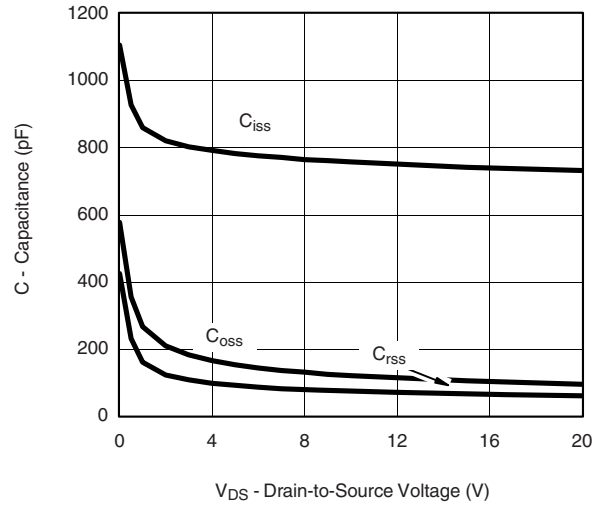
## TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$ , unless otherwise noted



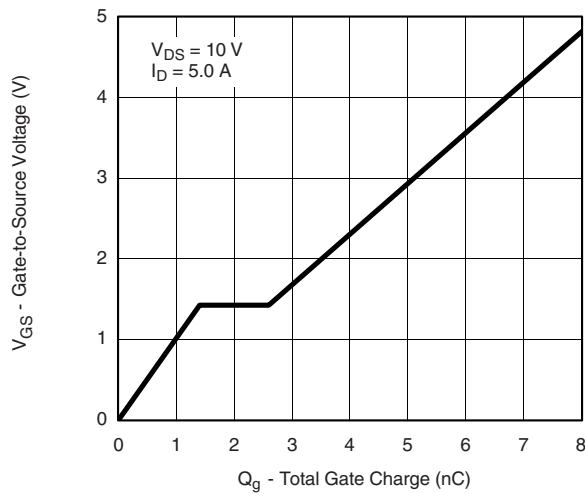
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



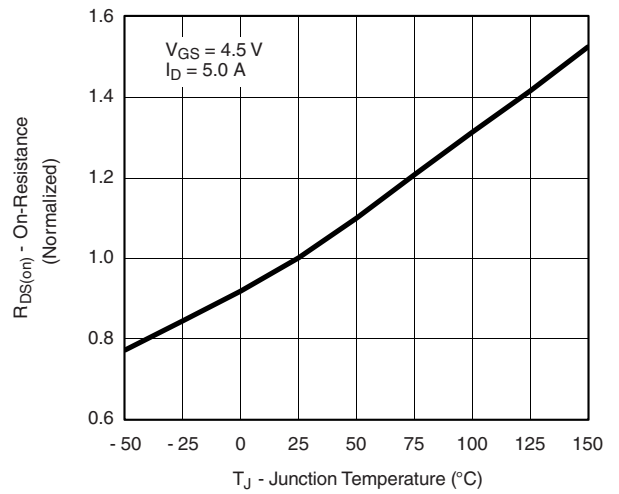
**On-Resistance vs. Drain Current**



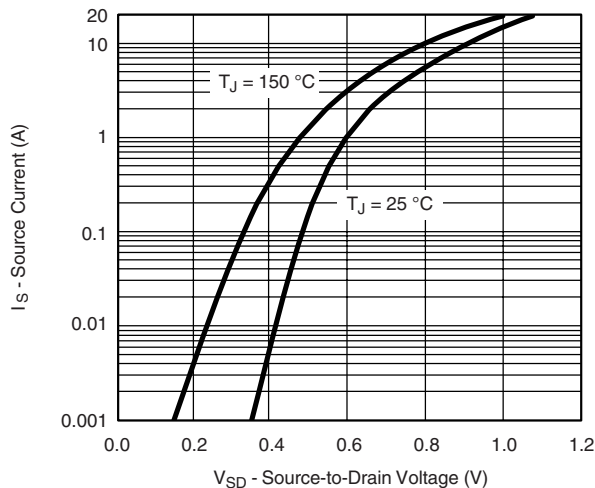
**Capacitance**



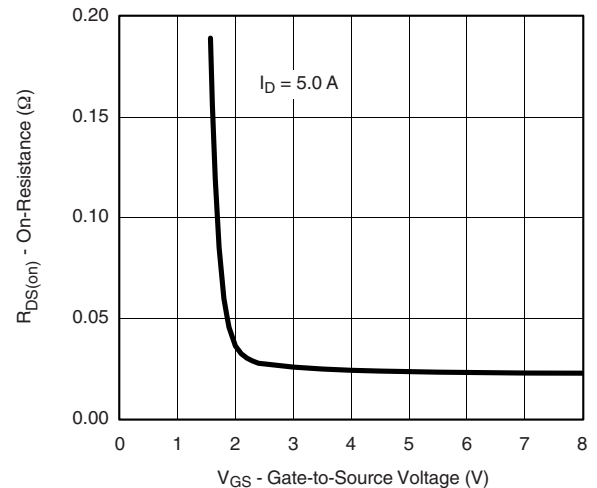
**Gate Charge**



**On-Resistance vs. Junction Temperature**

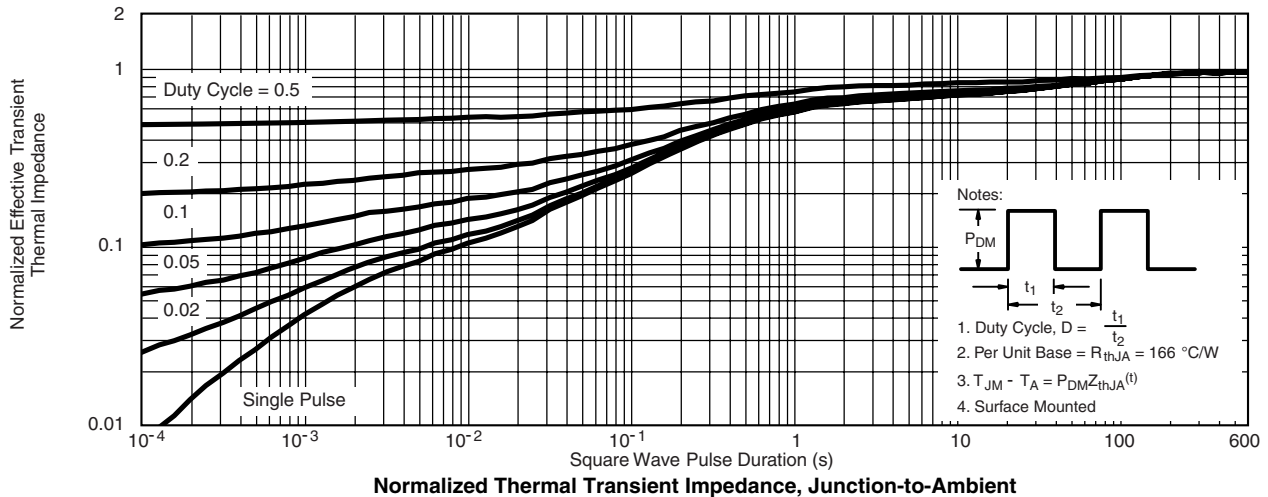
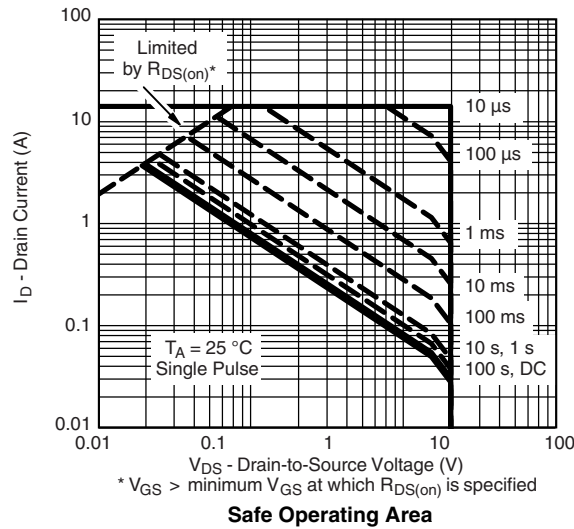
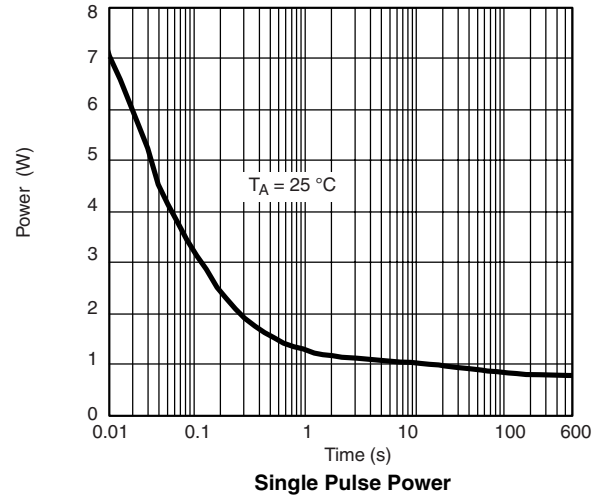
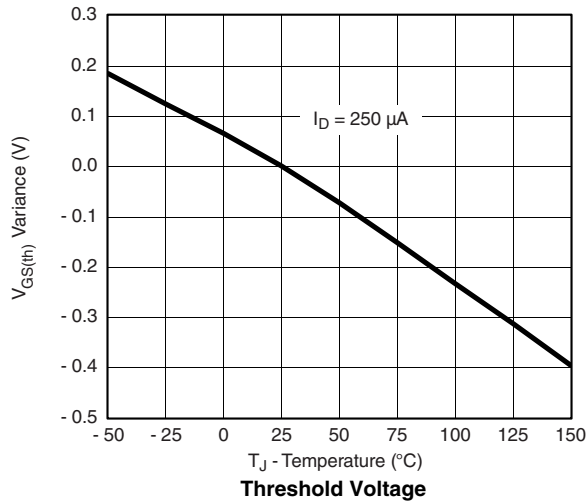


**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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